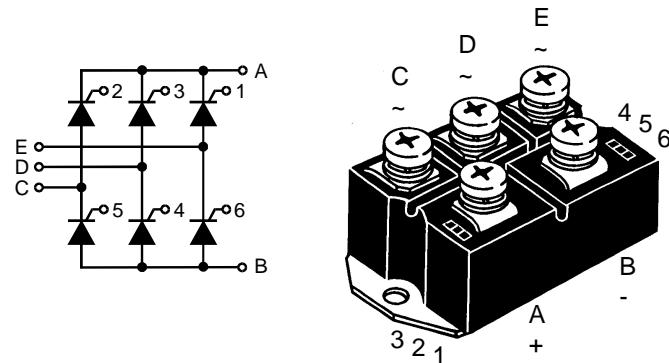


Three Phase Full Controlled Rectifier Bridge, B6C

$I_{dAVM} = 110/167 \text{ A}$
 $V_{RRM} = 1200-1600 \text{ V}$

V_{RSM}	V_{RRM}	Type
V_{DSM}	V_{DRM}	
V	V	
1300	1200	VTO 110-12io7
1500	1400	VTO 110-14io7
1700	1600	VTO 175-16io7
		VTO 175-12io7
		VTO 175-14io7
		VTO 175-16io7



Symbol	Test Conditions	Maximum Ratings		
		VTO 110	VTO 175	
I_{dAV}	$T_c = 85^\circ\text{C}$; module per leg	110 58	167 89	A
I_{FRMS}, I_{TRMS}	$T_{VJ} = 45^\circ\text{C}$; $t = 10 \text{ ms}$ (50 Hz), sine $V_R = 0$ $T_{VJ} = T_{VJM}$ $t = 10 \text{ ms}$ (50 Hz), sine $V_R = 0$	1150 1230	1500 1600	A
I_{FSM}, I_{TSM}	$t = 8.3 \text{ ms}$ (60 Hz), sine $t = 8.3 \text{ ms}$ (60 Hz), sine	1000 1070	1350 1450	A
I^2t	$T_{VJ} = 45^\circ\text{C}$ $t = 10 \text{ ms}$ (50 Hz), sine $V_R = 0$ $T_{VJ} = T_{VJM}$ $t = 10 \text{ ms}$ (50 Hz), sine $V_R = 0$	6600 6280	11200 10750	A^2s
	$t = 8.3 \text{ ms}$ (60 Hz), sine $t = 8.3 \text{ ms}$ (60 Hz), sine	5000 4750	9100 8830	A^2s
$(di/dt)_{cr}$	$T_{VJ} = T_{VJM}$ repetitive, $I_T = 50 \text{ A}$ $f = 400 \text{ Hz}$, $t_p = 200 \mu\text{s}$ $V_D = 2/3 V_{DRM}$ $I_G = 0.3 \text{ A}$, non repetitive $di_G/dt = 0.3 \text{ A}/\mu\text{s}$, $I_T = 1/3 \cdot I_{dAV}$	150	150	$\text{A}/\mu\text{s}$
$(dv/dt)_{cr}$	$T_{VJ} = T_{VJM}$; $V_{DR} = 2/3 V_{DRM}$ $R_{GK} = \infty$; method 1 (linear voltage rise)	1000	1000	$\text{V}/\mu\text{s}$
V_{RGM}		10	10	V
P_{GM}	$T_{VJ} = T_{VJM}$ $t_p = 30 \mu\text{s}$ $I_T = I_{TAVM}$ $t_p = 500 \mu\text{s}$ $t_p = 10 \text{ ms}$	\leq \leq \leq	10 5 1	W
P_{GAVM}		0.5	0.5	W
T_{VJ}		-40...+125	-40...+125	$^\circ\text{C}$
T_{VJM}		125	125	$^\circ\text{C}$
T_{stg}		-40...+125	-40...+125	$^\circ\text{C}$
V_{ISOL}	50/60 Hz, RMS $t = 1 \text{ min}$ $I_{ISOL} \leq 1 \text{ mA}$ $t = 1 \text{ s}$	2500 3000	2500 3000	V~
M_d	Mounting torque (M6) Terminal connection torque (M6)	5-15 5-15	5-15 5-15	Nm lb.in.
Weight	typ.	300	300	g

Data according to IEC 60747 and refer to a single thyristor/diode unless otherwise stated.
IXYS reserves the right to change limits, test conditions and dimensions.

Symbol	Test Conditions	Characteristic Values		
		VTO 110 VTO 175		
I_R, I_D	$V_R = V_{RRM}; V_D = V_{DRM}$ $T_{VJ} = T_{VJM}$ $T_{VJ} = 25^\circ C$	\leq	5 0.3	mA
V_F, V_T	$I_F, I_T = 200 A, T_{VJ} = 25^\circ C$	\leq	1.75	1.57 V
V_{TO}	For power-loss calculations only	0.85	0.85	V
r_T	$(T_{VJ} = 125^\circ C)$	6	3.5	$m\Omega$
V_{GT}	$V_D = 6 V; T_{VJ} = 25^\circ C$ $T_{VJ} = -40^\circ C$	\leq	1.5 1.6	V
I_{GT}	$V_D = 6 V; T_{VJ} = 25^\circ C$ $T_{VJ} = -40^\circ C$	\leq	100 200	mA
V_{GD}	$T_{VJ} = T_{VJM}; V_D = 2/3 V_{DRM}$	\leq	0.2	V
I_{GD}	$T_{VJ} = T_{VJM}; V_D = 2/3 V_{DRM}$	\leq	5	mA
I_L	$I_G = 0.3 A; t_G = 30 \mu s$ $T_{VJ} = 25^\circ C$ $di_G/dt = 0.3 A/\mu s$	\leq	450	mA
I_H	$T_{VJ} = 25^\circ C; V_D = 6 V; R_{GK} = \infty$	\leq	200	mA
t_{gd}	$T_{VJ} = 25^\circ C; V_D = 1/2 V_{DRM}$ $I_G = 0.3 A; di_G/dt = 0.3 A/\mu s$	\leq	2	μs
R_{thJC}	per thyristor (diode); DC current	0.65	0.46	K/W
	per module	0.108	0.077	K/W
R_{thJH}	per thyristor (diode); DC current	0.8	0.55	K/W
	per module	0.133	0.092	K/W
d_s	Creeping distance on surface	10		mm
d_A	Creepage distance in air	9.4		mm
a	Max. allowable acceleration	50		m/s^2

Dimensions in mm (1 mm = 0.0394")

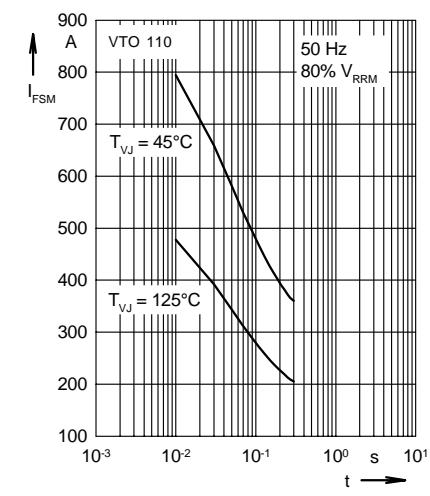
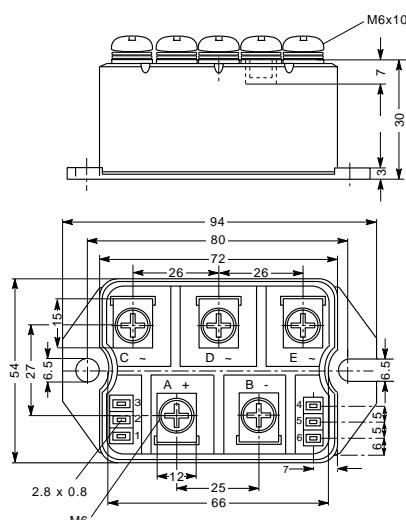


Fig. 3 Surge overload current
 I_{FSM} : Crest value, t : duration

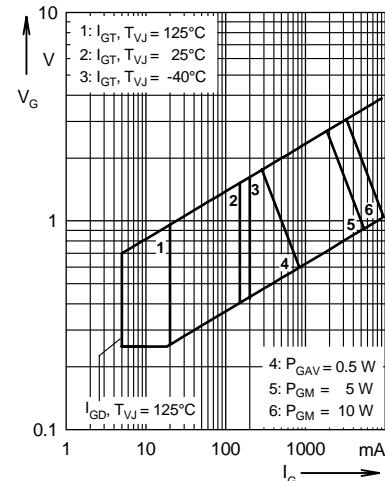


Fig. 1 Gate trigger characteristics

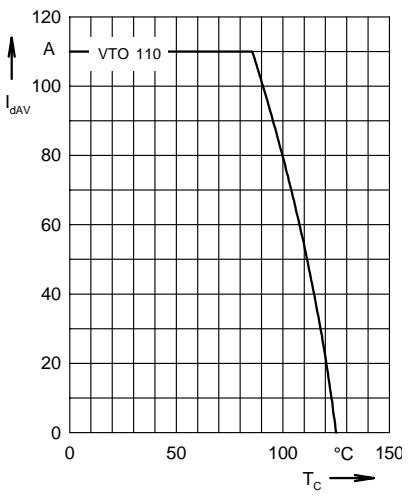


Fig. 2 DC output current at case temperature

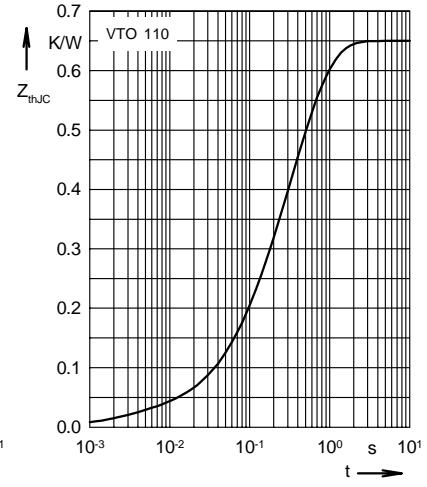


Fig. 4 Transient thermal impedance junction to case (per leg)